

# THYRISTOR MODULE

**200A / 1600V**

**PGH20016AM**

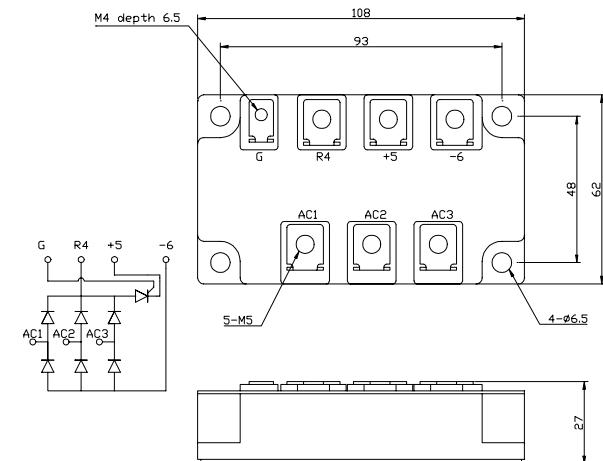
OUTLINE DRAWING

## FEATURES

- \* Isolated Base
- \* 3 Phase Converter with Rush-Current Controllable Thyristor
- \* High Surge Capability
- \* UL Recognized, File No. E187184

## TYPICAL APPLICATIONS

- \* Converter For UPS , VVVF and Servo Motor Drive Amplifier



Approx Net Weight: 530g

## Part of Diode Bridge and Thyristor Maximum Ratings

| Parameter                            |                    | Conditions                                 |                 | Max Rated Value | Unit       |
|--------------------------------------|--------------------|--|-----------------|-----------------|------------|
| Average Rectified Output Current     | I <sub>O(AV)</sub> | 3 Phase Full Wave Rectified                |                 | 200             | A          |
|                                      |                    | Tc=90°C(Non-Bias)                          | Tc=65°C(Biased) |                 |            |
| Operating Junction Temperature Range | T <sub>jw</sub>    | Tj>125°C, Can not be Biased for Thyristor. |                 | -40 to +150     | °C         |
| Storage Temperature Range            | T <sub>stg</sub>   |  |                 | -40 to +125     | °C         |
| Isolation Voltage                    | V <sub>iso</sub>   | Base Plate to Terminals, AC1min.           |                 | 2500            | V          |
| Mounting torque                      | Case mounting      | F <sub>tor</sub>                           | Greased         | M6 Screw        | 2.5 to 3.5 |
|                                      | Terminals          |  |                 | M6 Screw        | 2.5 to 3.5 |
|                                      |                    |  |                 | M4 Screw        | 1.2 to 1.6 |

## Thermal Characteristics

| Characteristics    | Symbol               | Test Conditions             | Maximum Value. | Unit |
|--------------------|----------------------|-----------------------------|----------------|------|
| Thermal Resistance | R <sub>th(c-f)</sub> | Case to Fin, Total, Greased | 0.06           | °C/W |

## Part of Diode Bridge (6 dies)

### Maximum Ratings

| Parameter                              | Symbol           | Grade      | Unit |
|--|------------------|------------|------|
|  |                  | PGH20016AM |      |
| Repetitive Peak Reverse Voltage *1     | V <sub>RRM</sub> | 1600       | V    |
| Non Repetitive Peak Reverse Voltage *1 | V <sub>RSM</sub> | 1700       |      |

| Parameter                     | Symbol           | Conditions                                   | Max Rated Value | Unit             |
|-------------------------------|------------------|--|-----------------|------------------|
| Surge Forward Current *1      | I <sub>FSM</sub> | 50 Hz Half Sine Wave, 1Pulse, Non-Repetitive | 1800            | A                |
| I Squared t *1                | I <sup>2</sup> t | 2msec to 10msec                              | 16200           | A <sup>2</sup> s |
| Allowable Operating Frequency | f                |  | 400             | Hz               |

\*1 Value Per 1 Arm

## Electrical • Thermal Characteristics

| Characteristics         | Symbol               | Test Conditions   | Maximum Value. | Unit |
|-------------------------|----------------------|---|----------------|------|
| Peak Reverse Current *1 | I <sub>RM</sub>      | V <sub>RM</sub> = V <sub>RRM</sub> , T <sub>j</sub> = 125°C | 20             | mA   |
| Peak Forward Voltage *1 | V <sub>FM</sub>      | I <sub>FM</sub> = 200A, T <sub>j</sub> =25°C                | 1.35           | V    |
| Thermal Resistance      | R <sub>th(j-c)</sub> | Junction to Case (Total)                                    | 0.10           | °C/W |

\*1 Value Per 1 Arm

### Part of Thyristor (1 die)

#### Maximum Ratings

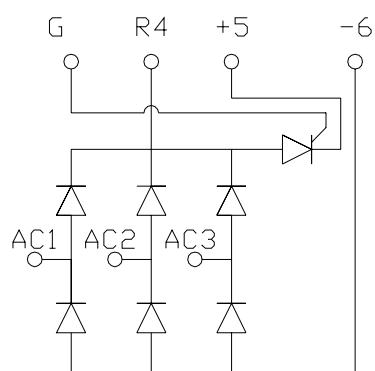
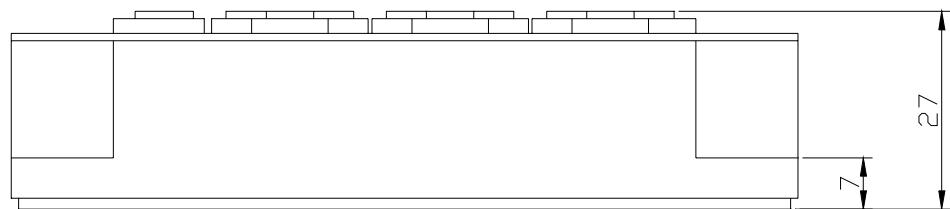
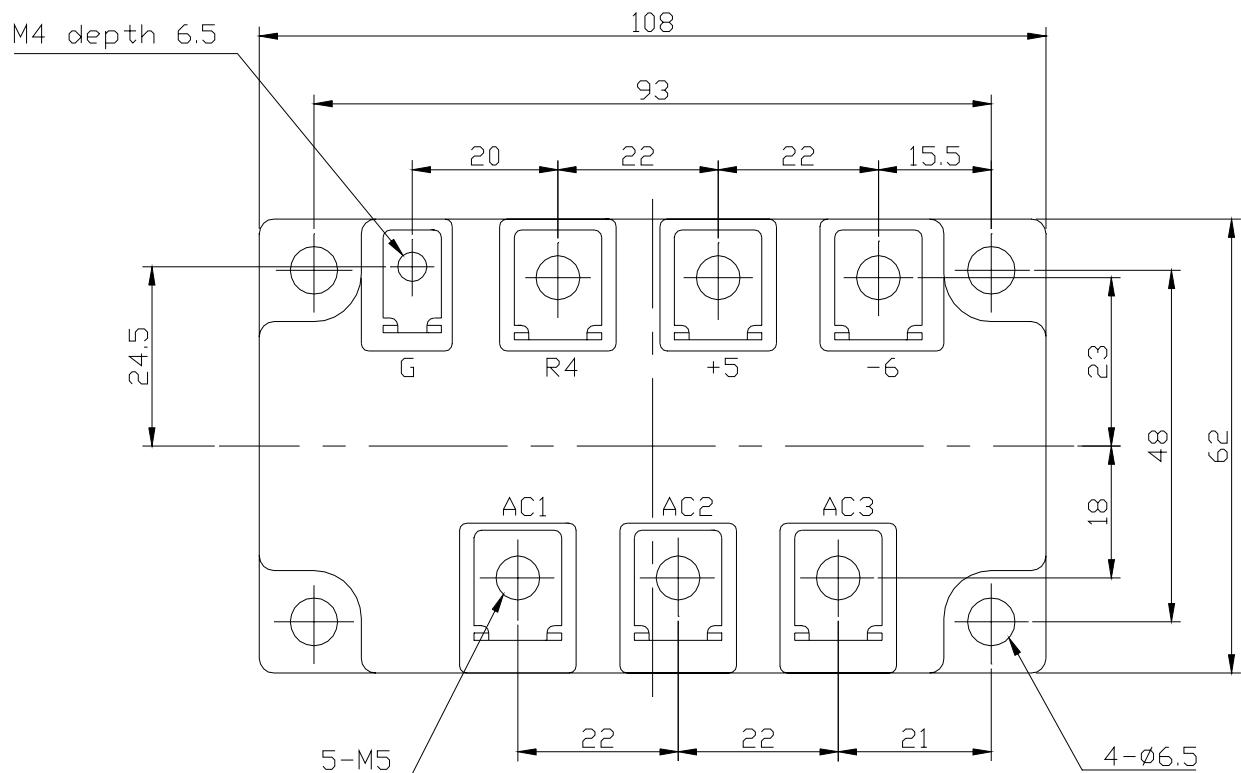
| Parameter                             | Symbol            | Grade      | Unit |
|---------------------------------------|-------------------|------------|------|
|                                       |                   | PGH20016AM |      |
| Repetitive Peak Off-State Voltage     | V <sub>DRM</sub>  | 1600       | V    |
| Non Repetitive Peak Off-State Voltage | V <sub>DSDM</sub> | 1700       |      |
| Repetitive Peak Reverse Voltage       | V <sub>RRM</sub>  | 1600       | V    |
| Non Repetitive Peak Reverse Voltage   | V <sub>RSM</sub>  | 1700       |      |

| Parameter                          |                    | Conditions  | Max Rated Value | Unit             |
|------------------------------------|--------------------|---|-----------------|------------------|
| Surge On-State Current             | I <sub>TSM</sub>   | 50 Hz Half Sine Wave, 1Pulse Non-Repetitive   | 3200            | A                |
| I Squared t                        | I <sup>2</sup> t   | 2msec to 10msec   | 51200           | A <sup>2</sup> s |
| Critical Rate of Turned-On Current | di/dt              | V <sub>D</sub> =2/3V <sub>DRM</sub> , I <sub>TM</sub> =2·I <sub>O</sub> , T <sub>j</sub> =125°C<br>I <sub>G</sub> =300mA, di/dt=0.2A/μs | 100             | A/μs             |
| Peak Gate Power                    | P <sub>GM</sub>    |   | 5               | W                |
| Average Gate Power                 | P <sub>G(AV)</sub> |   | 1               | W                |
| Peak Gate Current                  | I <sub>GM</sub>    |   | 2               | A                |
| Peak Gate Voltage                  | V <sub>GM</sub>    |   | 10              | V                |
| Peak Gate Reverse Voltage          | V <sub>RGM</sub>   |   | 5               | V                |

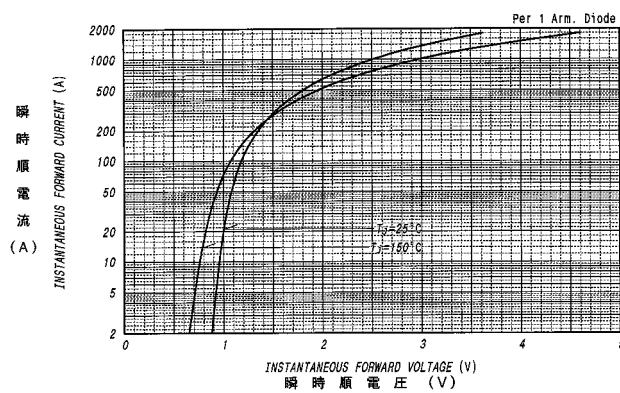
#### Electrical • Thermal Characteristics

| Characteristics                            | Symbol               | Test Conditions   | Maximum Value.        |      |      | Unit |
|--|----------------------|---|-----------------------|------|------|------|
|  |                      |   | Min.                  | Typ. | Max. |      |
| Peak Off-State Current                     | I <sub>DM</sub>      | V <sub>DM</sub> = V <sub>DRM</sub> , T <sub>j</sub> = 125°C   |                       |      | 50   | mA   |
| Peak Reverse Current                       | I <sub>RM</sub>      | V <sub>RM</sub> = V <sub>RRM</sub> , T <sub>j</sub> = 125°C   |                       |      | 50   | mA   |
| Peak On-State Voltage                      | V <sub>TM</sub>      | I <sub>TM</sub> = 200A, T <sub>j</sub> =25°C  |                       |      | 1.35 | V    |
| Gate Current to Trigger                    | I <sub>GT</sub>      | V <sub>D</sub> =6V, I <sub>T</sub> =1A  | T <sub>j</sub> =-40°C |      | 300  | mA   |
|  |                      |   | T <sub>j</sub> =25°C  |      | 150  |      |
|  |                      |   | T <sub>j</sub> =125°C |      | 80   |      |
| Gate Voltage to Trigger                    | V <sub>GT</sub>      | V <sub>D</sub> =6V, I <sub>T</sub> =1A  | T <sub>j</sub> =-40°C |      | 5.0  | V    |
|  |                      |   | T <sub>j</sub> =25°C  |      | 3.0  |      |
|  |                      |   | T <sub>j</sub> =125°C |      | 2.0  |      |
| Gate Non-Trigger Voltage                   | V <sub>GD</sub>      | V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C   | 0.25                  |      |      | V    |
| Critical Rate of Rise of Off-State Voltage | dv/dt                | V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C   | 500                   |      |      | V/μs |
| Turn-Off Time                              | t <sub>q</sub>       | I <sub>TM</sub> =I <sub>O</sub> , V <sub>D</sub> =2/3V <sub>DRM</sub><br>dv/dt=20V/μs, V <sub>R</sub> =100V<br>-di/dt=20A/μs, T <sub>j</sub> =125°C |                       | 150  |      | μs   |
| Turn-On Time                               | t <sub>gt</sub>      | V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C<br>I <sub>G</sub> =300mA, di/dt=0.2A/μs   |                       | 6    |      | μs   |
| Delay Time                                 | t <sub>d</sub>       |   |                       | 2    |      | μs   |
| Rise Time                                  | t <sub>r</sub>       |   |                       | 4    |      | μs   |
| Latching Current                           | I <sub>L</sub>       | T <sub>j</sub> =25°C  |                       | 150  |      | mA   |
| Holding Current                            | I <sub>H</sub>       | T <sub>j</sub> =25°C  |                       | 100  |      |      |
| Thermal Resistance                         | R <sub>th(j-c)</sub> | Junction to Case  |                       |      | 0.25 | °C/W |

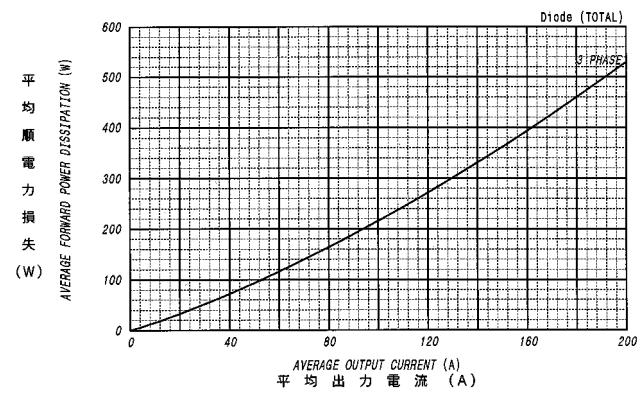
## PGH20016AM OUTLINE DRAWING (Dimensions in mm)



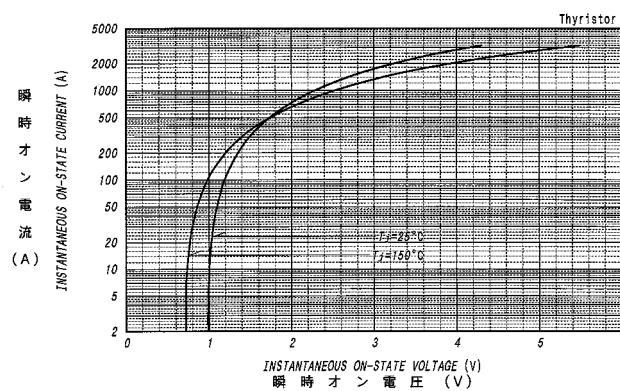
順電圧特性  
FORWARD CURRENT VS. VOLTAGE



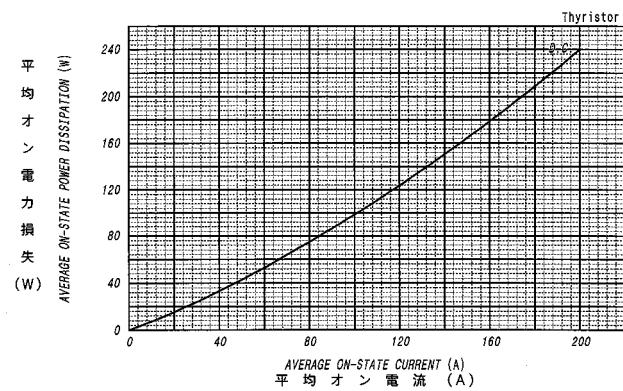
平均順電力損失特性  
AVERAGE FORWARD POWER DISSIPATION



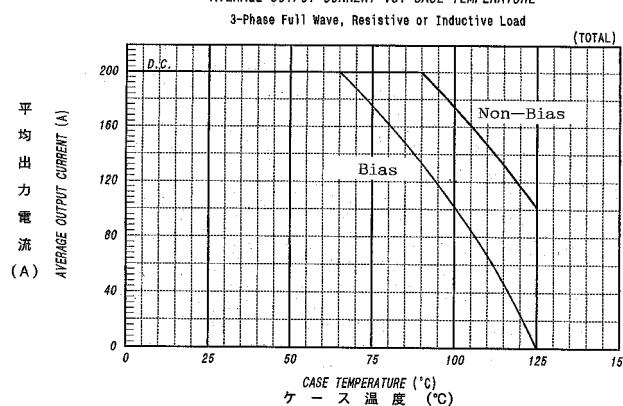
オン電圧特性  
ON-STATE CURRENT VS. VOLTAGE



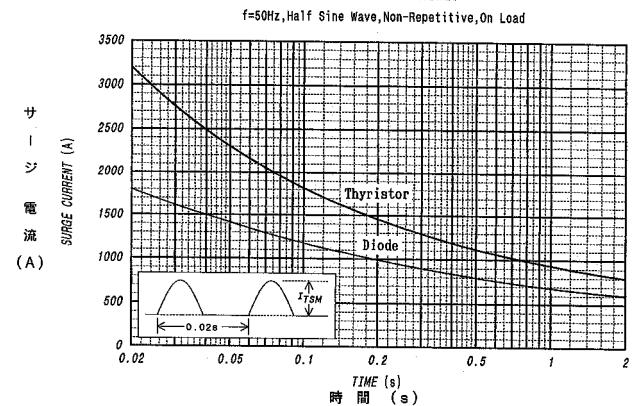
平均オン電力損失特性  
AVERAGE ON-STATE POWER DISSIPATION



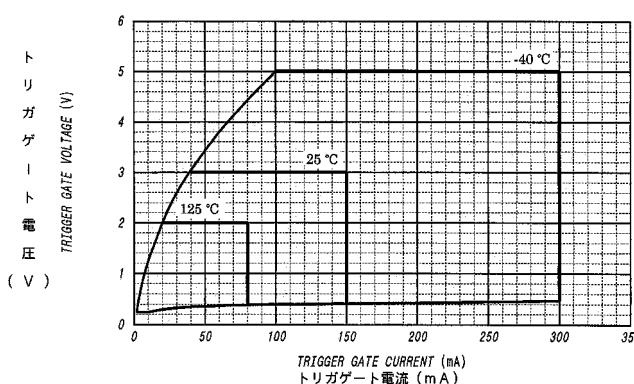
平均出力電流 - ケース温度定格  
AVERAGE OUTPUT CURRENT VS. CASE TEMPERATURE



サージ電流定格  
SURGE CURRENT RATINGS



ゲート特性  
GATE CHARACTERISTICS



ゲート定格  
GATE RATINGS

